

# **Opt-Pass Sensor**

**Preliminary** 

#### **■ GENERAL DESCRIPTION**

The NJL9101R is the high-precision optical position sensor, which is combine with a super luminosity RED LED and Si light-sensitive element into small package. Three sine waves with high precision phase difference will output by using the dedicated striped mirror (NJL9600 series). By arithmetic processing of the sensor output signal, the position detection with high precision and high resolution can be performed.

The characteristics by optical scheme are not affected from the magnetic field of magnet that built into the motor etc The Opt-Pass (NJL9101R,NJL9600 series) sensor has been designed strongly against the distance variation between the sensor and the special striped mirror. Also the Opt-pass has been designed against the tilt variation.

# **■ FEATURES**

Output voltage: 90mVp-p typ. (0°, 90°,180°) @IF=5mA, VCE=3.3V,RL=2KΩ,d=0.7mm,NJL9601MD

• Miniature, thin package : 2.3mm × 2.0mm × 0.6mm

• Low operating dark current : 0.5μA max.

• Pb free solder re-flowing permitted : 255°C, 2times

• Built-in function of visible light cut-off filter

#### **■ APPLICATIONS**

- Detecting the location of AF Lens unit for DSC,DVC
- Detecting the location of Zoom Lens unit for DSC,DVC
- Positioning for high precision

# ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Emitter Forward Current (Continuous) Reverse Voltage (Continuous) Power Dissipation	lf	15	mA
	VR	6	V
	PD	45	mW
Detector Collector-Emitter Voltage Emitter-Collector Voltage Collector Current Collector Power Dissipation	VCEO	16	V
	VECO	6	V
	IC	10	mA
	PC	25	mW
Coupled Total Power Dissipation Operating Temperature Storage Temperature Reflow Soldering Temperature	Ptot	60	mW
	Topr	-30 to +70	°C
	Tstg	-30 to +85	°C
	Tsol	255	°C

#### ■ RECOMMENDED OPERATING CONDITION

PARAMETER	SYMBOL	RATINGS	UNIT
Forward Current	lF	5	mA
Collector-Emitter Voltage	VCEO	+2.0 to +3.3	V
Power Dissipation	Gap	0.7	mm

NOTICE: This product is under development. The content of data sheet is subject to change prior notice.

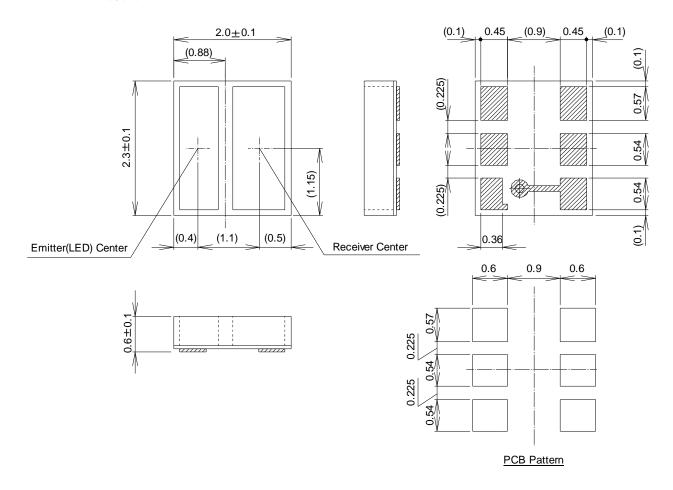


■ ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Emitter						
Forward Voltage	VF	IF=5mA	1.1	1.4	1.7	V
Reverse Current	IR	VR=6V	_	_	1	μΑ
Detector						
Dark Current	ICEO	VCE=5V	_	_	0.5	μΑ
Collector-Emitter Voltage	VCEO	IC=100μA	16	_	_	V
Coupled						
Output Current 1 *1	IO1	IF=5mA,VCE=3.3V,d=0.7mm(Al Mirror)*1	TBD	(400)	TBD	μΑ
Output Current 2 *1	IO2	IF=5mA,VCE=3.3V,d=0.7mm(Al Mirror)*1	TBD	(400)	TBD	μΑ
Output Current 3 *1	IO3	IF=5mA,VCE=3.3V,d=0.7mm(Al Mirror)*1	TBD	(400)	TBD	μΑ
Operating Dark Current 1	ICEOD1	IF=5mA,VCE=3.3V	_	_	(0.5)	μΑ
Operating Dark Current 2	ICEOD2	IF=5mA,VCE=3.3V	_	_	(0.5)	μΑ
Operating Dark Current 3	ICEOD3	IF=5mA,VCE=3.3V	_	_	(0.5)	μΑ
Output Voltage 1 *2	Vo1	IF=5mA,VCE=3.3V,RL=2K $\Omega$ ,d=0.7mm*2	_	90	_	mVp-p
Output Voltage 2 *2	Vo2	IF=5mA,VCE=3.3V,RL=2K $\Omega$ ,d=0.7mm*2	_	90	_	mVp-p
Output Voltage 3 *2	Vo3	IF=5mA,VCE=3.3V,RL=2K $\Omega$ ,d=0.7mm*2	_	90	_	mVp-p
Phase Difference2	Vo2p	Phase Difference to Output Voltage1	_	90	_	deg
Phase Difference3	Vo3p	Phase Difference to Output Voltage2	_	180	_	deg
Cut -off Frequency	fc	VCE=3.3V,RL=2K $\Omega$ ,-3dB	_	20	_	kHz

<sup>\*1</sup> Output Current is the value obtained that is used the reflective board of Aluminum Evaporation

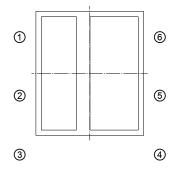
# ■ OUTLINE (typ.) Unit : mm



<sup>\*2</sup> Output Voltage is the value obtained that is used the dedicated striped mirror (NJL9601MD).



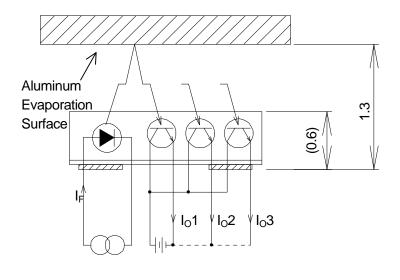
#### **■ PIN LAYOUT**



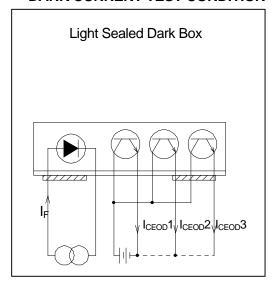
- ① Cathode (LED)

- (a) Catriode (LED)
  (b) Anode (LED)
  (c) Emitter1 (Out1)
  (d) Emitter2 (Out2)
  (e) Collector (Common Out1,2,3)
  (e) Emitter3 (Out3)

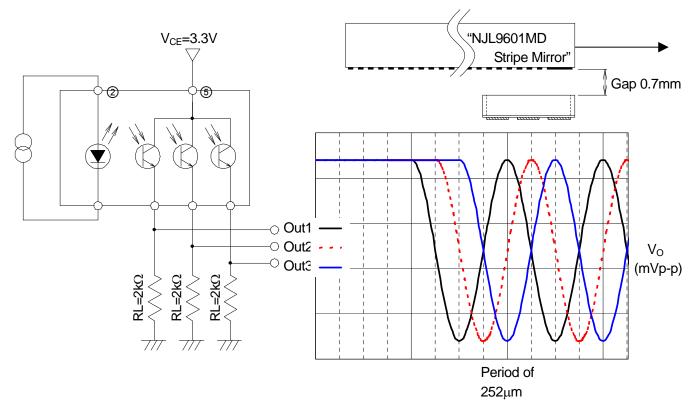
# ■ OUTPUT CURRENT TEST CONDITION



# ■ DARK CURRENT TEST CONDITION

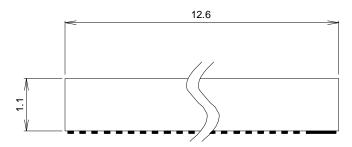


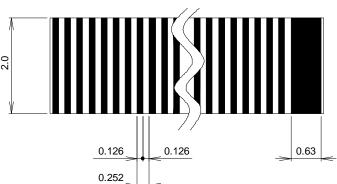
# ■ OUTPUT VOLTAGE TEST CONDITION





# ■ NJL9101R STRIPED MIRROR OUTLINE (typ.)





Unit: mm

• Outline Tolerance

• Dimension for Pattern of

Original position detection

• Dimension for Reflective Pattern

• Dimension for Non-Reflective Pattern

• Pattern Pitch

• Recommend detection distance

±0.05mm

0.63mm±0.002mm

0.126mm±0.002mm

0.126mm±0.002mm

0.252mm

10mm



# ■ MOUNTING METHOD

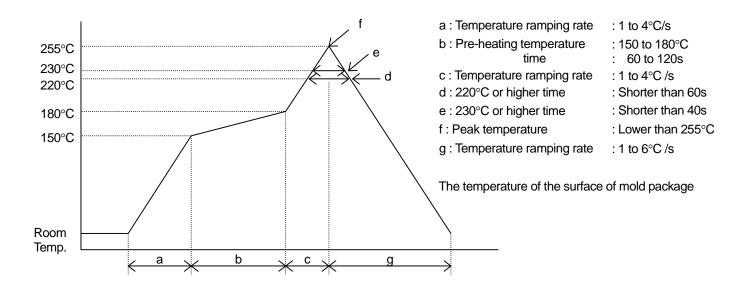
#### NOTE

Mounting was evaluated with the following profiles in our company, so there was no problem. However, confirm mounting by the condition of your company beforehand.

Mounting: Twice soldering is allowed.

#### ■ INFRARED REFLOW SOLDERING METHOD

#### Recommended reflow soldering procedure



(NOTE1) Using reflow furnace with short wave infrared radiation heater such as halogen lamp Regarding temperature profile, please refer to those fo reflow furnace.

In this case the resin surface temperature may become higher than lead terminals due to endothermic ally of black colored mold resin. Therefore, please avoid from direct exposure to mold resin.

# (NOTE2) Other method

Such other methods of soldering as dipping the device into melted solder and vapor phase method (VPS) are not appropriate because the body of device will be heated rapidly. Therefore, these are not recommended to apply.

(NOTE3) The resin gets softened right after soldering, so, the following care has to be taken Not to contact the lens surface to anything.

Not to dip the device into water or any solvents.

#### ■ FLOE SOLDERING METHOD

Flow soldering is not possible.

#### ■ IRON SOLDERING METHOD

Iron soldering is not possible.



#### CLEANING

Avid washing the device after soldering by reflow method.

# ■ IC STORAGE CONDITIONS AND ITS DURATION

(1) Temperature and humidity ranges

Pack Sealing Temperature: 5 to 40 [°C]

Humidity: 40 to 80 [%]

Pack Opening Temperature: 5 to 30 [°C]

Humidity: 40 to 70 [%]

After opening the bag, solder products within 48h.

Avoid a dry environment below 40% because the products are is easily damageable by the electrical discharge.

Store the products in the place where it does not create dew with the products due to a sudden change in temperature.

- (2) When baking, place the reel vertically to avoid load to the side.
- (3) Do not store the devices in corrosive-gas atmosphere.
- (4) Do not store the devices in a dusty place.
- (5) Do not expose the devices to direct rays of the sun.
- (6) Do not allow external forces or loads to be applied to IC's.
- (7) BE careful because affixed label on the reel might be peeled off when baking.

#### ■ BAKING

In case of keeping expect above condition be sure to apply baking. (Heat-resistant tape)

Baking method: Ta=60°C, 48 to 72h, Three times baking is allowed

Ta=100°C, 2 to 6h, Three times baking is allowed

# ■ STORAGE DURATION

Within a year after delivering this device.

For the products stored longer than a year, confirm their terminals and solderability before they are used.

# ■ APPLICATION NOTES

(1) Attention in handling

Treat not to touch the lens surface.

Avoid dust and any other foreign materials on the lens surface such as point, bonding material, etc.

Never to apply reverse voltage (VEC) of more than 6V on the photo transistor when measuring the characteristics or adjusting the system. If applied, it causes to lower the sensitivity.

When mounting, special care has to be taken on the mounting position and tilting of the device because it is very important to place the device to the optimum position to the object.

[CAUTION]

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